

PSMN4R3-100PS

N-channel 100 V 4.3 m Ω standard level MOSFET in TO-220

Rev. 1 — 27 October 2011

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see Figure 1	[1]	-	-	120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	338	W
T _j	junction temperature			-55	-	175	°C
Static charac	teristics						
R _{DSon} drain-source on-state resistance	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12		-	6.6	7.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	[2]	-	3.7	4.3	mΩ
Dynamic cha	racteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 75 \text{ A}; V_{DS} = 50 \text{ V};$		-	49	-	nC
Q _{G(tot)}	total gate charge	see Figure 14; see Figure 15		-	170	-	nC
Avalanche ru	ggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; $V_{sup} \le$ 100 V; R_{GS} = 50 Ω ; Unclamped		-	-	537	mJ

^[1] Continuous current limited by package



[2] Measured 3 mm from package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AR)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R3-100PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _i ≥ 25 °C; T _i ≤ 175 °C		-	100	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ		-	100	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	$V_{GS} = 10 \text{ V}; T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{}$		-	119	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	<u>[1]</u>	-	120	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3		-	673	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	338	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drai	in diode					
Is	source current	T _{mb} = 25 °C	<u>[1]</u>	-	120	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	673	Α
Avalanche r	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 100 V; R_{GS} = 50 Ω ; Unclamped		-	537	mJ

[1] Continuous current limited by package

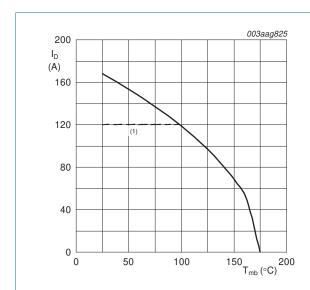


Fig 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10 V$; (1) Capped at 120A due to package

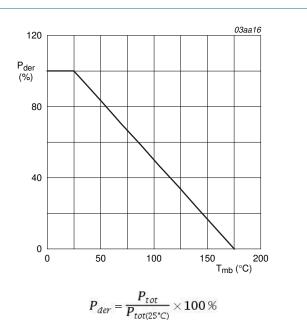
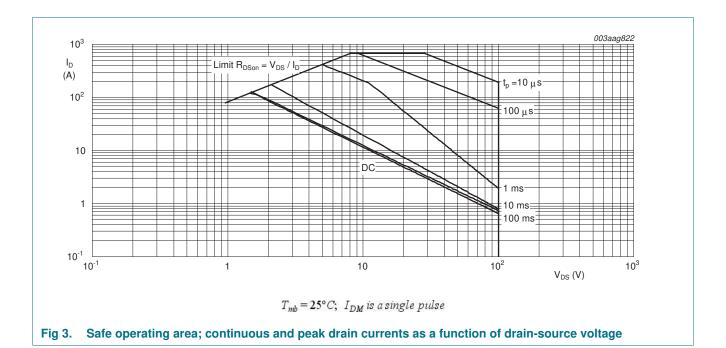


Fig 2. Normalized total power dissipation as a function of mounting base temperature



Thermal characteristics

Table 5. **Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.44	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W



6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	100	-	-	V
	voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	-	-	4.6	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 10	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.08	10	μΑ
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μΑ
I_{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12	-	10.4	12	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C};$ see Figure 12	-	6.6	7.8	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	1 -	3.7	4.3	mΩ
R _G	gate resistance	f = 1 MHz	-	0.9	-	Ω
Dynamic o	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 75 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 15	-	170	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	140	-	nC
Q _{GS}	gate-source charge	$I_D = 75 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V}; \text{see}$	-	48	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	Figure 14; see Figure 15	-	31	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	17.3	-	nC
Q_{GD}	gate-drain charge		-	49	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V _{DS} = 50 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	5.1	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	9900	-	pF
Coss	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	660	-	pF
C _{rss}	reverse transfer capacitance		-	381	-	pF
d(on)	turn-on delay time	V_{DS} = 50 V; R_L = 0.67 Ω ; V_{GS} = 10 V;	-	45	-	ns
r	rise time	$R_{G(ext)} = 4.7 \Omega; I_D = 75 A; T_j = 25 °C$	-	91	-	ns
d(off)	turn-off delay time		-	122	-	ns
t _f	fall time		-	63	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain	n diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 17	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$;	-	75	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	235	-	nC

[1] Measured 3 mm from package.

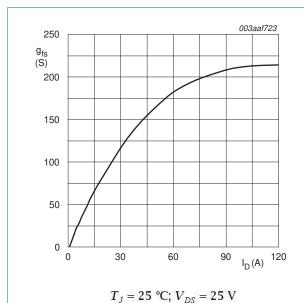


Fig 5. Forward transconductance as a function of drain current; typical values

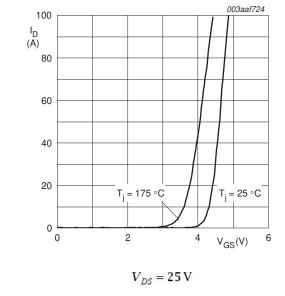


Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

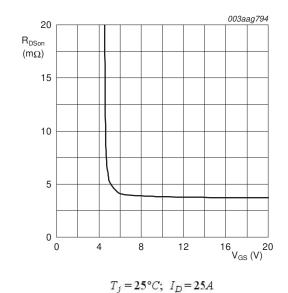


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

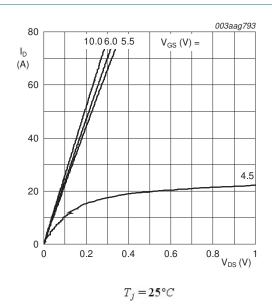


Fig 8. Output characteristics; drain current as a function of drain-source voltage; typical values

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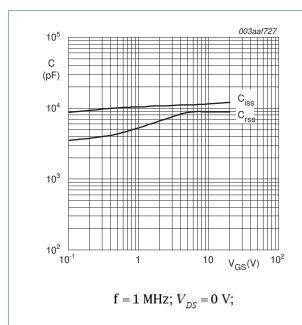


Fig 9. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

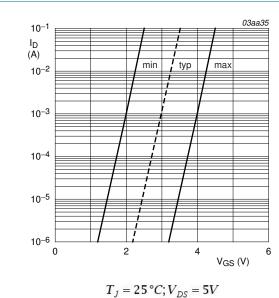


Fig 11. Sub-threshold drain current as a function of gate-source voltage

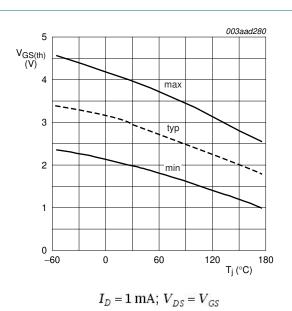


Fig 10. Gate-source threshold voltage as a function of junction temperature

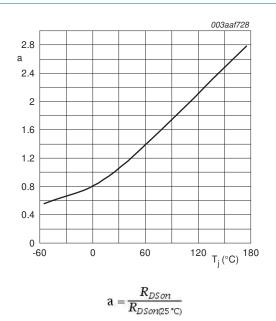
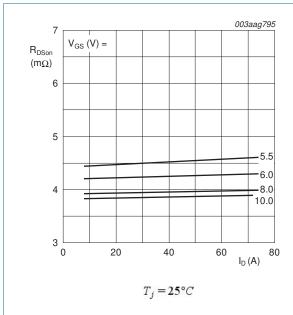


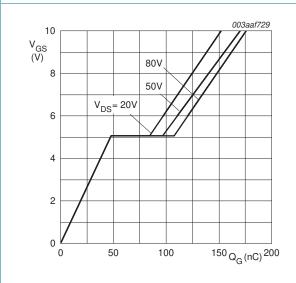
Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

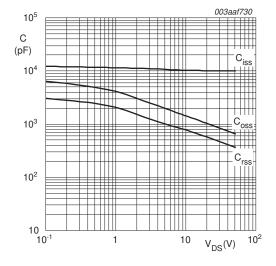


V_{GS}(pl)
V_{GS}(th)
V_{GS}
Q_{GS1} Q_{GS2}
Q_{GS} Q_G(tot)
003aaa508

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

Fig 14. Gate charge waveform definitions





 $T_j = 25$ °C; $I_D = 75$ A

Fig 16. Input, output and reverse transfer capacitances

Fig 15. Gate-source voltage as a function of gate charge; typical values

as a function of drain-source voltage; typical values

 $V_{GS} = 0 \text{ V}; f = 1 \text{MHz}$

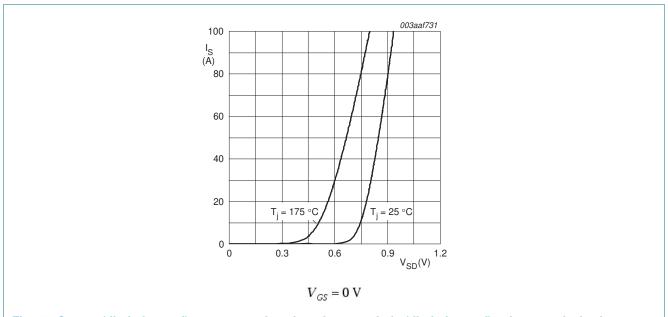
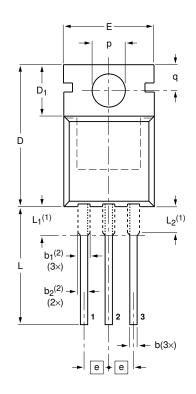
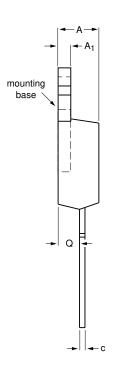


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB SOT78





0 5 10 mm

DIMENSIONS (mm are the original dimensions)

ι	JNIT	Α	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q
	mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	1990E DATE	
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13	

Fig 18. Package outline SOT78 (TO-220AB)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R3-100PS v.1	20111027	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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